



September 2014

FCP170N60

N-Channel SuperFET[®] II MOSFET

600 V, 22 A, 170 mΩ

Features

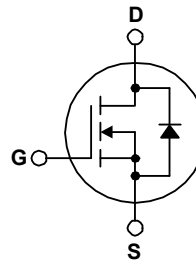
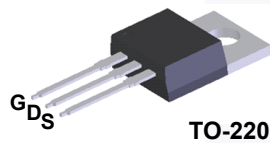
- 650 V @T_J = 150°C
- Typ. R_{DS(on)} = 150 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 42 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 190 pF)
- 100% Avalanche Tested
- RoHS Compliant

Applications

- Telecom / Server Power Supplies
- Industrial Power Supplies
- AC-DC Power Supply

Description

SuperFET[®] II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is suitable for various AC/DC power conversion for system miniaturization and higher efficiency.



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted.

| Symbol | Parameter | FCP170N60 | Unit |
|-----------------------------------|--|---------------------------------------|------|
| V _{DSS} | Drain to Source Voltage | 600 | V |
| V _{GSS} | Gate to Source Voltage | - DC | V |
| | | - AC | |
| I _D | Drain Current | - Continuous (T _C = 25°C) | A |
| | | - Continuous (T _C = 100°C) | |
| I _{DM} | Drain Current | - Pulsed (Note 1) | 66 |
| E _{AS} | Single Pulsed Avalanche Energy | (Note 2) | 525 |
| I _{AR} | Avalanche Current | (Note 1) | 5 |
| E _{AR} | Repetitive Avalanche Energy | (Note 1) | 2.27 |
| dv/dt | MOSFET dv/dt | (Note 3) | V/ns |
| | Peak Diode Recovery dv/dt | | |
| P _D | Power Dissipation | (T _C = 25°C) | 227 |
| | | - Derate above 25°C | 1.82 |
| T _J , T _{STG} | Operating and Storage Temperature Range | -55 to +150 | °C |
| T _L | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds | 300 | °C |

Thermal Characteristics

| Symbol | Parameter | FCP170N60 | Unit |
|------------------|---|-----------|------|
| R _{θJC} | Thermal Resistance, Junction to Case, Max. | 0.55 | °C/W |
| R _{θJA} | Thermal Resistance, Junction to Ambient, Max. | 40 | |

Package Marking and Ordering Information

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|-----------|---------|----------------|-----------|------------|----------|
| FCP170N60 | FCP170N60 | TO-220 | Tube | N/A | N/A | 50 units |

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|-----------------|------|------|------|------|
|--------|-----------|-----------------|------|------|------|------|

Off Characteristics

| | | | | | | |
|--------------------------------|---|---|-----|------|-----------|---------------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$ | 600 | - | - | V |
| | | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}, T_J = 150^\circ\text{C}$ | 650 | - | - | V |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = 10\text{ mA}$, Referenced to 25°C | - | 0.67 | - | $\text{V}/^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$ | - | - | 1 | μA |
| | | $V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_C = 125^\circ\text{C}$ | - | 1.2 | - | |
| I_{GSS} | Gate to Body Leakage Current | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | - | - | ± 100 | nA |

On Characteristics

| | | | | | | |
|--------------|--------------------------------------|---|-----|-----|-----|------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$ | 2.5 | - | 3.5 | V |
| $R_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10\text{ V}, I_D = 11\text{ A}$ | - | 150 | 170 | $\text{m}\Omega$ |
| g_{FS} | Forward Transconductance | $V_{DS} = 20\text{ V}, I_D = 11\text{ A}$ | - | 17 | - | S |

Dynamic Characteristics

| | | | | | | | |
|------------------|-------------------------------|---|--------------------|------|------|----|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$ | - | 2150 | 2860 | pF | |
| C_{oss} | Output Capacitance | | - | 60 | 80 | pF | |
| C_{rss} | Reverse Transfer Capacitance | | - | 2.65 | - | pF | |
| $C_{oss (eff.)}$ | Effective Output Capacitance | $V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$ | - | 190 | - | pF | |
| $Q_{g(tot)}$ | Total Gate Charge at 10V | $V_{DS} = 380\text{ V}, I_D = 11\text{ A},$ $V_{GS} = 10\text{ V}$ | - | 42 | 55 | nC | |
| Q_{gs} | Gate to Source Gate Charge | | - | 9 | - | nC | |
| Q_{gd} | Gate to Drain "Miller" Charge | | (Note 4) | - | 11 | - | nC |
| ESR | Equivalent Series Resistance | | $f = 1\text{ MHz}$ | - | 0.95 | - | Ω |

Switching Characteristics

| | | | | | | |
|--------------|---------------------|--|----------|----|-----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 380\text{ V}, I_D = 11\text{ A},$ $V_{GS} = 10\text{ V}, R_g = 4.7\text{ }\Omega$ | - | 21 | 50 | ns |
| t_r | Turn-On Rise Time | | - | 12 | 35 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | - | 55 | 120 | ns |
| t_f | Turn-Off Fall Time | | (Note 4) | - | 3.8 | 18 |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|--|--|---|-----|-----|---------------|
| I_S | Maximum Continuous Drain to Source Diode Forward Current | - | - | 22 | A | |
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | - | - | 66 | A | |
| V_{SD} | Drain to Source Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_{SD} = 11\text{ A}$ | - | - | 1.2 | V |
| t_{rr} | Reverse Recovery Time | $V_{GS} = 0\text{ V}, I_{SD} = 11\text{ A},$ | - | 346 | - | ns |
| Q_{rr} | Reverse Recovery Charge | $di_F/dt = 100\text{ A}/\mu\text{s}$ | - | 6.2 | - | μC |

Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature
2. $I_{AS} = 5\text{ A}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 11\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq 380\text{ V}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature typical characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

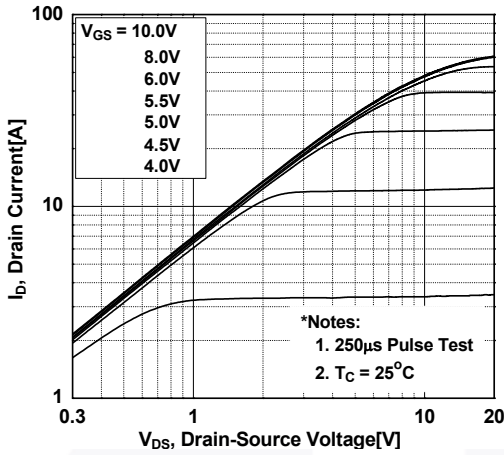


Figure 2. Transfer Characteristics

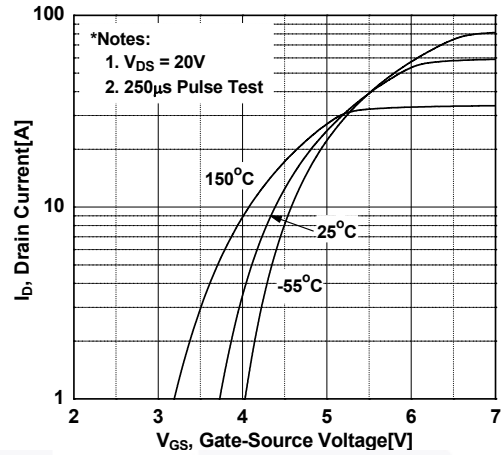


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

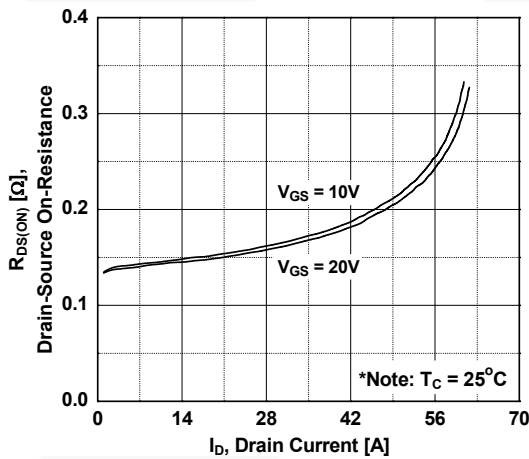


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

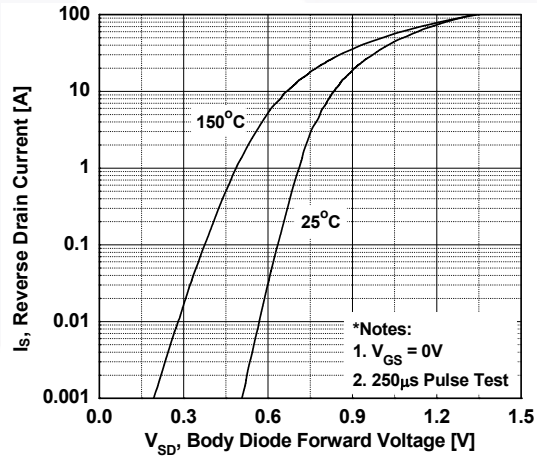


Figure 5. Capacitance Characteristics

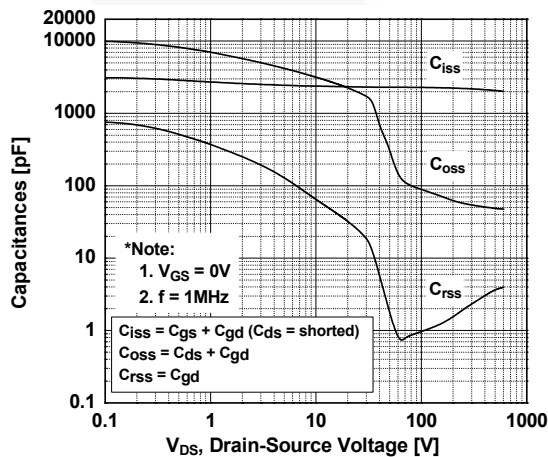
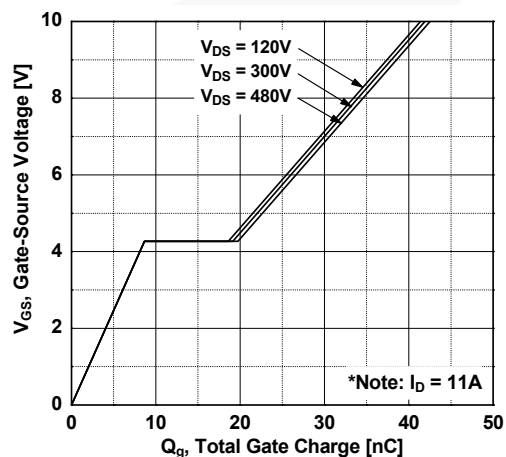


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

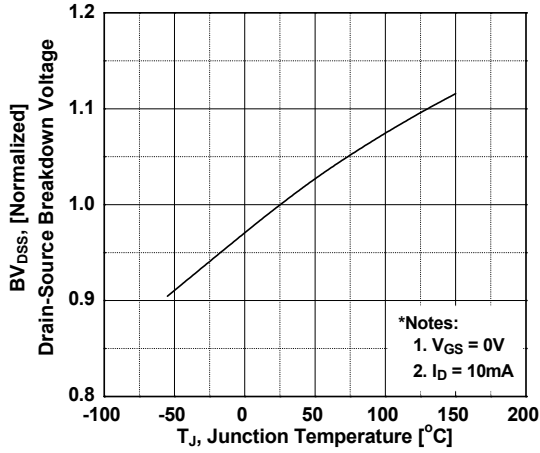


Figure 8. On-Resistance Variation vs. Temperature

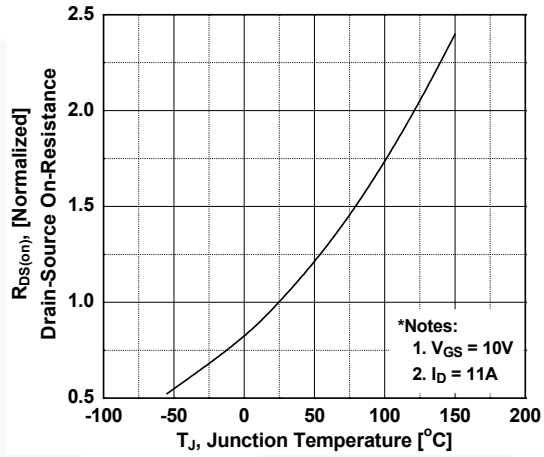


Figure 9. Maximum Safe Operating Area

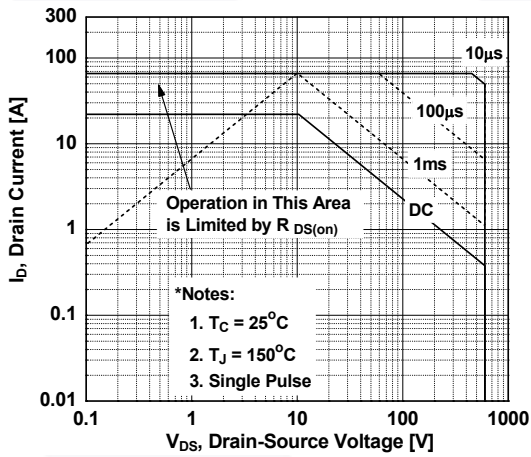


Figure 10. Maximum Drain Current vs. Case Temperature

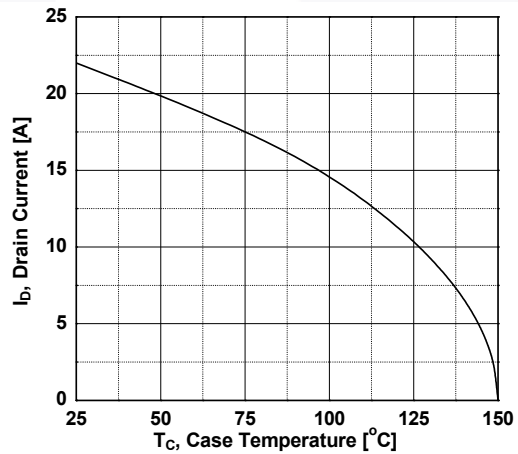
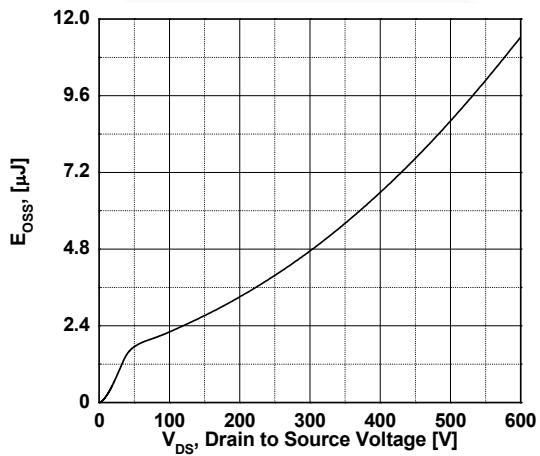
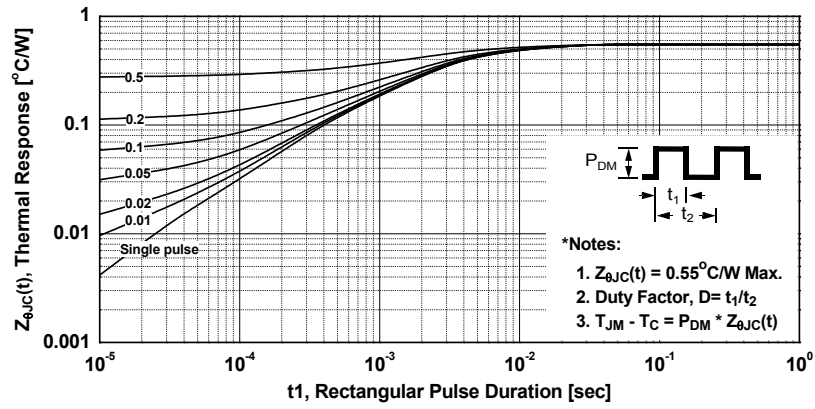


Figure 11. E_oss vs. Drain to Source Voltage



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



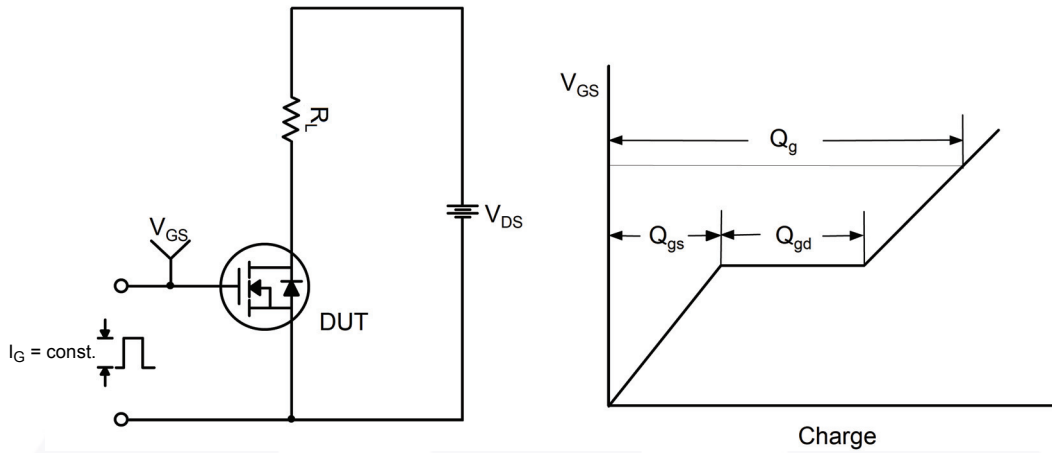


Figure 13. Gate Charge Test Circuit & Waveform



Figure 14. Resistive Switching Test Circuit & Waveforms

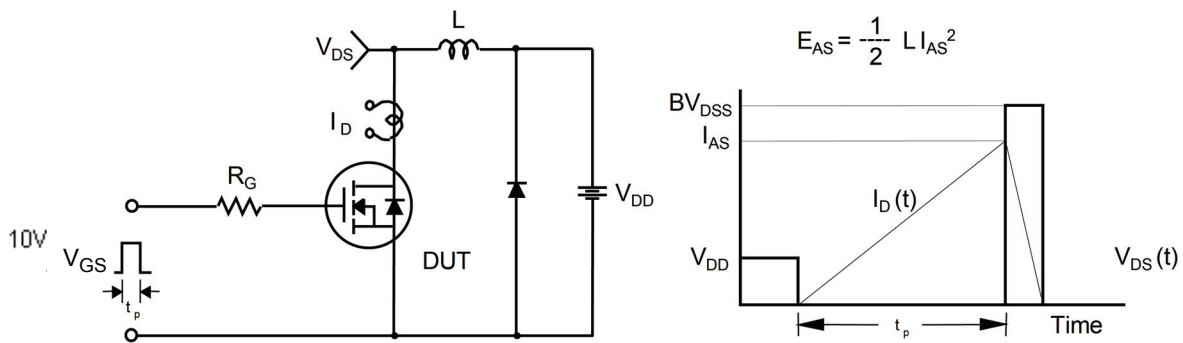


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

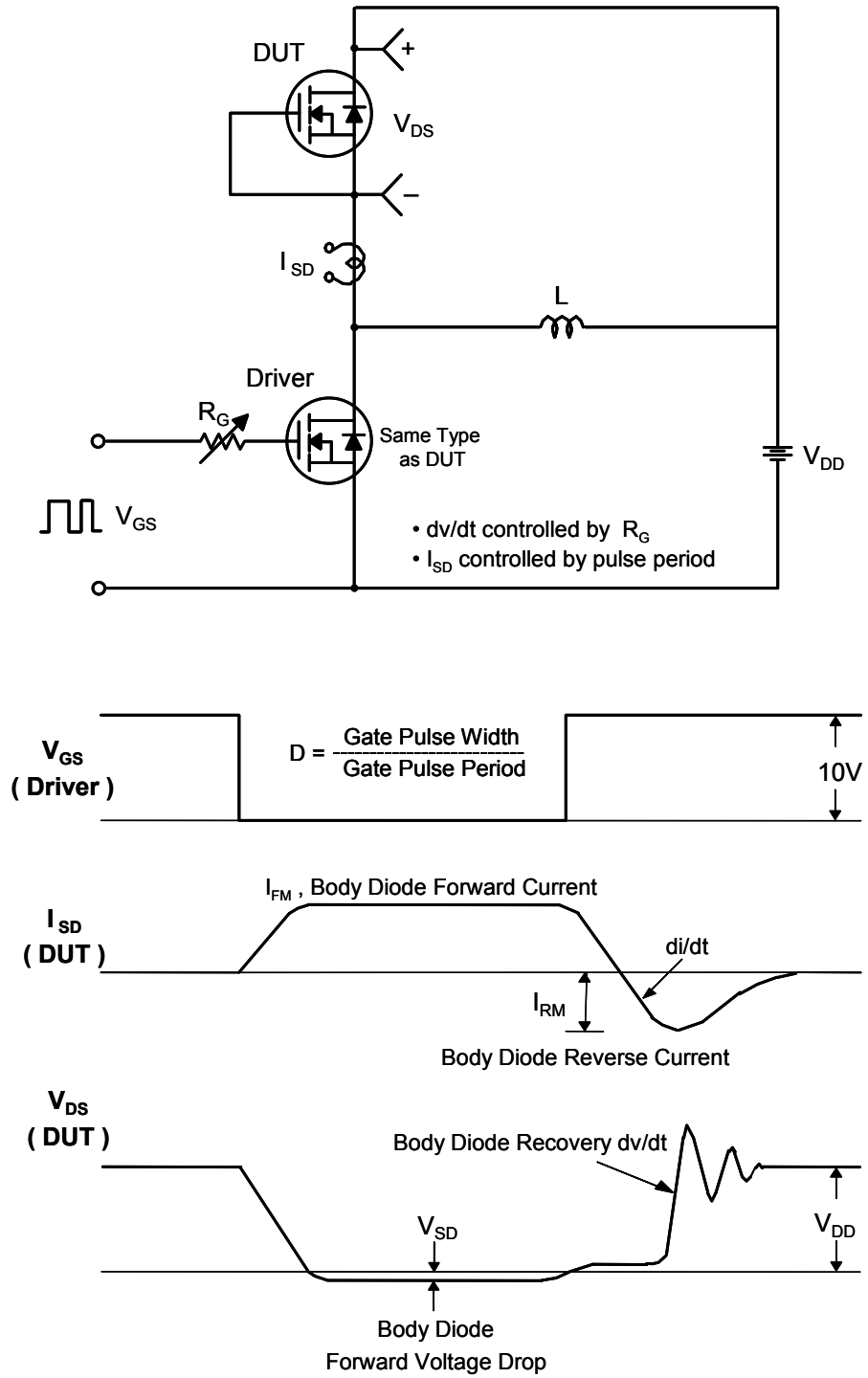


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms



- NOTES:**
- A) REFERENCE JEDEC, TO-220, VARIATION AB
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [].
 - D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
 - E) DOES NOT COMPLY JEDEC STANDARD VALUE.
 - F) "A1" DIMENSIONS AS BELOW:
 SINGLE GAUGE = 0.51 - 0.61
 DUAL GAUGE = 1.10 - 1.45
 - G) DRAWING FILE NAME: TO220B03REV9
 - H) PRESENCE IS SUPPLIER DEPENDENT
 - I) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

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